General Purpose Transistor

PNP Silicon

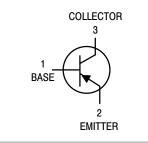
Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-45	Vdc
Collector–Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-800	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

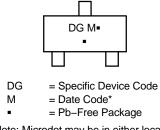
Characteristic	Symbol	Max	Unit	
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^{\circ}C$	PD	225	mW	
Derate above 25°C		1.8	mW/°C	
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W	
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^{\circ}C$	P _D	300	mW	
Derate above 25°C		2.4	m₩/°C	
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	°C/W	
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C	

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in 99.5% alumina.



MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BCW68GLT1G, NSVBCW68GLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BCW68GLT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel

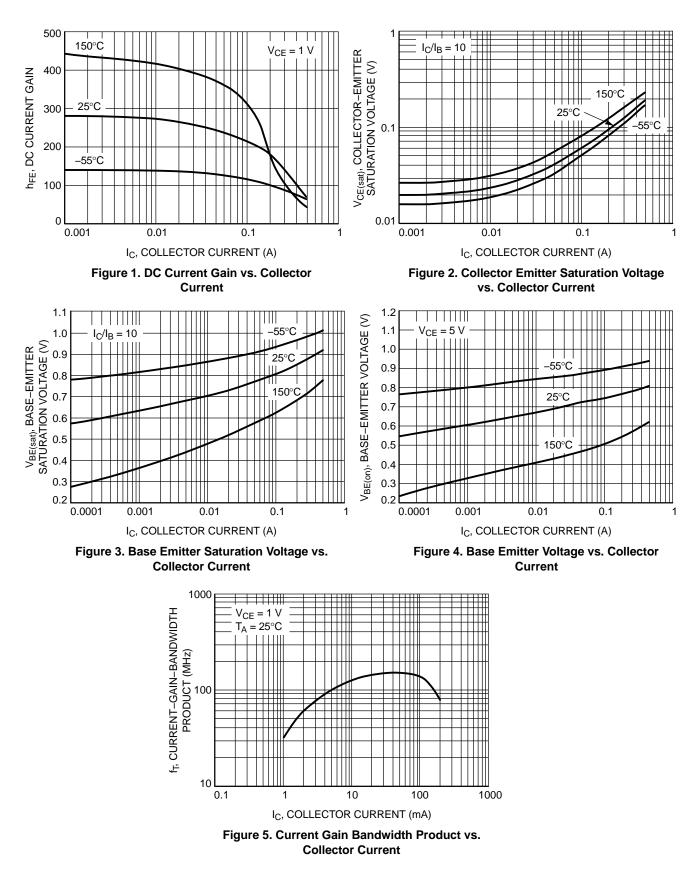
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

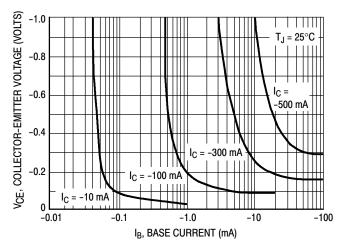
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Emitter Breakdown Voltage $(I_C = -10 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-45	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = -10 \ \mu Adc, \ V_{EB} = 0)$	V _{(BR)CES}	-60	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	-	-	Vdc
Collector Cutoff Current $(V_{CE}=-45 \text{ Vdc}, I_E = 0)$ $(V_{CE}=-45 \text{ Vdc}, I_B = 0, T_A = 150^{\circ}\text{C})$	ICES			-20 -10	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = -4.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	-	-20	nAdc
ON CHARACTERISTICS					•
DC Current Gain ($I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -300 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)	h _{FE}	120 160 60	_ _ _	400 _ _	-
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc}$)	V _{CE(sat)}	-	-	-0.7	Vdc
Base–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc}$)	V _{BE(sat)}	-	-	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS		*			•
Current–Gain – Bandwidth Product ($I_c = -20$ mAdc, $V_{CE} = -10$ Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance $(V_{CB}$ = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	-	18	pF
Input Capacitance $(V_{EB}=-0.5 \text{ Vdc}, I_C=0, f=1.0 \text{ MHz})$	C _{ibo}	-	-	105	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	N _F	-	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS





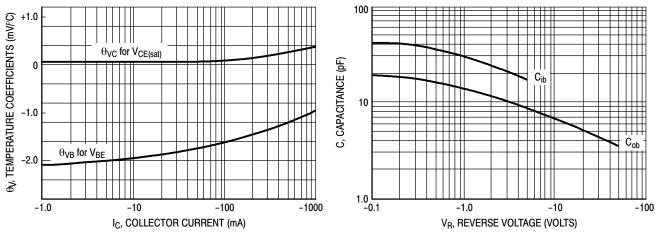
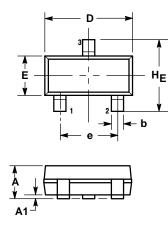


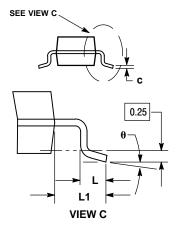
Figure 7. Temperature Coefficients

Figure 8. Capacitances

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**





NOTES

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 1.

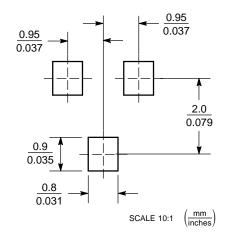
- 2 3.
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 198 CONTROLLING DIMENSION: INCH. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, DISTRIBUTION OF CATER DURING MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
ΗE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6 PIN 1. BASE 2 EMITTER

> 3 COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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